TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSII)

2SK3442

Switching Regulator, DC-DC Converter and Motor Drive Applications

• Low drain-source ON resistance: $RDS(ON) = 15 \text{ m}\Omega \text{ (typ.)}$

• High forward transfer admittance: $|Y_{fs}| = 28 \text{ S (typ.)}$

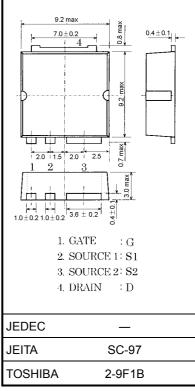
• Low leakage current: $IDSS = 100 \mu A (VDS = 100 V)$

• Enhancement-mode: $V_{th} = 2.0 \sim 4.0 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA})$

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	100	V	
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	100	V	
Gate-source voltage		V _{GSS}	±30	V	
Drain current	DC (Note 1)	I _D	45	А	
	Pulse (Note 1)	I _{DP}	180		
Drain power dissipation (Tc = 25°C)		P _D	125	W	
Single pulse avalanche energy (Note 2)		E _{AS}	468	mJ	
Avalanche current		I _{AR}	45	Α	
Repetitive avalanche energy (Note 3)		E _{AR}	12.5	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

Unit: mm



Weight: 0.74 g (typ.)

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	1.00	°C/W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

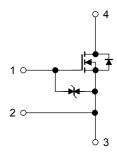
Note 2 V_{DD} = 25 V, T_{ch} = 25°C (initial), L = 373 μ H, R_{G} = 25 Ω , I_{AR} = 45 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.



Please use the S1 pin for gate input signal return. Make sure that the main current flows into S2 pin.





Electrical Characteristics (Note 4) (Ta = 25°C)

Chara	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$	_		±10	μΑ
Drain cut-off current		I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V	_	_	100	μА
Drain-source brea	kdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	100	_	_	V
Gate threshold vo	ltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	_	4.0	V
Drain-source ON	resistance	R _{DS (ON)}	V _{GS} = 10 V, I _D = 23 A	_	15	20	mΩ
Forward transfer a	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 23 A	14	28	_	S
Input capacitance		C _{iss}		_	4100	_	
Reverse transfer capacitance		C _{rss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	340	_	pF
Output capacitance		C _{oss}		_	980	_	
Switching time -	Rise time	t _r	V_{GS} 0 V V_{GS} 0 V $0 V$	_	15	_	- ns
	Turn-on time	t _{on}		_	45	_	
	Fall time	t _f		_	20	_	
	Turn-off time	t _{off}		_	95	_	
Total gate charge (gate-source plus gate-drain)		Qg	$V_{DD} \simeq 80 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 45 \text{ A}$		85		nC
Gate-source charge		Q_{gs}		_	50	_	
Gate-drain ("miller") charge		Q _{gd}		_	35	_	

Note 4: Please connect the S1 pin and S2 pin, and then ground the connected pin.

(However, while switching times are measured, please don't connect and ground it.)

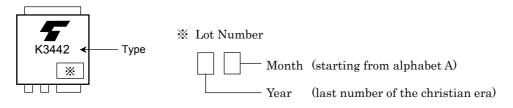
Source-Drain Ratings and Characteristics (Note 5) (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1, Note 5)	I _{DR} 1	_		_	45	Α
Pulse drain reverse current (Note 1, Note 5)	I _{DRP} 1	_			180	Α
Continuous drain reverse current (Note 1, Note 5)	I _{DR} 2	_	_	_	1	Α
Pulse drain reverse current (Note 1, Note 5)	I _{DRP} 2	_	_	_	4	Α
Forward voltage (diode)	V _{DS2F}	I _{DR} = 45 A, V _{GS} = 0 V	_	_	-1.5	V
Reverse recovery time	t _{rr}	$I_{DR} = 45 \text{ A}, V_{GS} = 0 \text{ V},$	_	160	_	ns
Reverse recovery charge	Q _{rr}	$dI_{DR}/dt = 50 A/\mu s$	_	512	_	nC

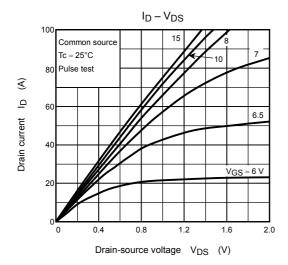
Note 5: I_{DR1} , I_{DRP1} : drain, flowing current value between the S2 pin, open the S1 pin I_{DR2} , I_{DRP2} : drain, flowing current value between the S1 pin, open the S2 pin

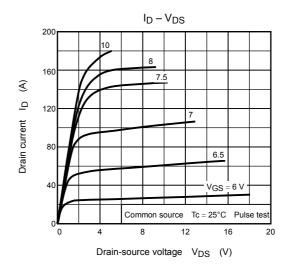
Unless otherwise specified, please connect the S1 and S2 pins, and then ground the connected pin.

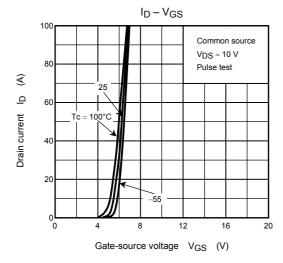
Marking

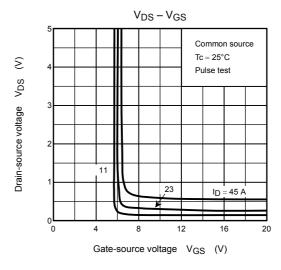


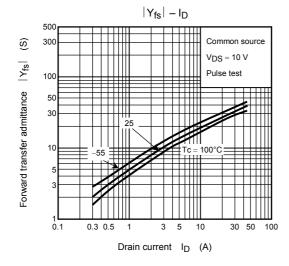
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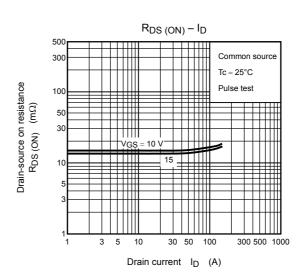




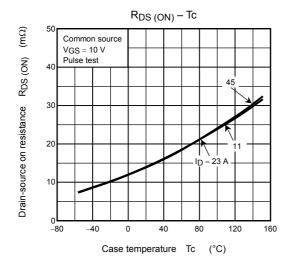


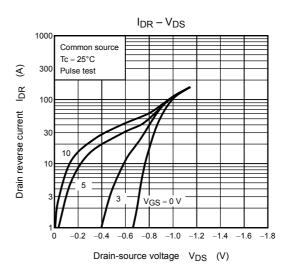


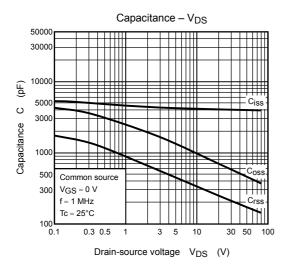


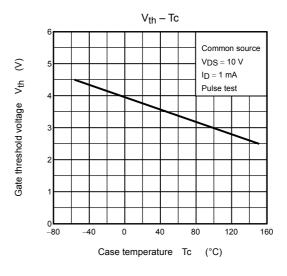


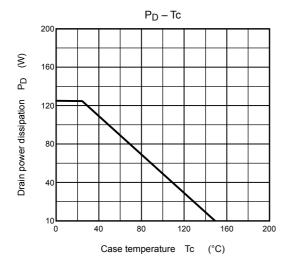
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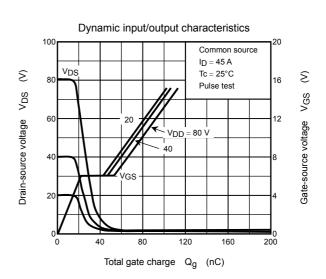




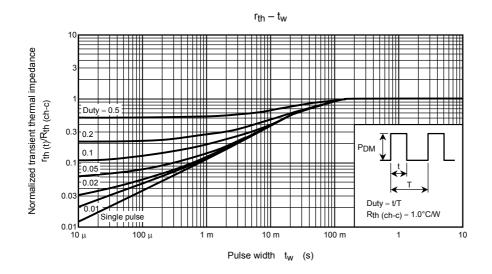


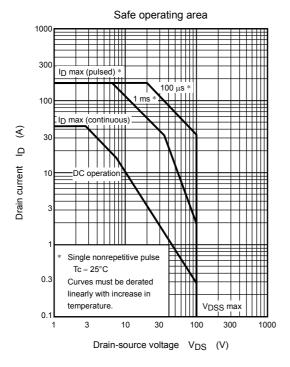


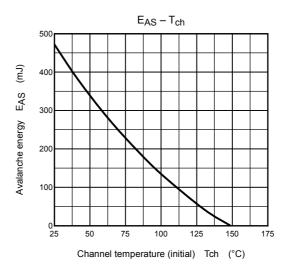


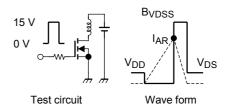


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$$\begin{aligned} &R_G = 25~\Omega \\ &V_{DD} = 25~V,~L = 373~\mu H \end{aligned} \qquad \text{EAS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - VDD} \right) \end{aligned}$$

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